

## Vishay Semiconductors

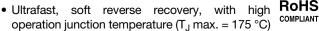
## **Insulated Ultrafast Rectifier Module, 80 A**



PRODUCT SUMMARY	
$V_R$	600 V
I <sub>F(AV)</sub> per module at T <sub>C</sub> = 104 °C	80 A
t <sub>rr</sub>	34 ns
Туре	Modules - Diode FRED Pt®
Package	SOT-227

#### **FEATURES**

- Two fully independent diodes
- Fully insulated package





- Low forward voltage drop
- · Optimized for power conversion: welding and industrial SMPS applications
- Easy to use and parallel
- · Industry standard outline
- UL approved file E78996



- · Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see www.vishav.com/doc?99912

### **DESCRIPTION**

The VS-UFB80FA60 insulated modules integrate two state of the art ultrafast recovery rectifiers in the compact, industry standard SOT-227 package. The diodes structure, and its life time control, provide an ultrasoft recovery current shape, together with the best overall performance, ruggedness and reliability characteristics.

These devices are thus intended for high frequency applications in which the switching energy is designed not to be predominant portion of the total energy, such as in the output rectification stage of welding machines, SMPS, DC/DC converters. Their extremely optimized stored charge and low recovery current reduce both over dissipation in the switching elements (and snubbers) and EMI/RFI.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Cathode to anode voltage	V <sub>R</sub>		600	V
Continuous forward current per diode	I <sub>F</sub>	T <sub>C</sub> = 85 °C	57	Α
Single pulse forward current per diode	I <sub>FSM</sub>	T <sub>C</sub> = 25 °C	280	A
Maximum power dissipation per module	P <sub>D</sub>	T <sub>C</sub> = 85 °C	174	W
RMS isolation voltage	V <sub>ISOL</sub>	Any terminal to case, t = 1 minute	2500	V
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		- 55 to 175	°C



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<b>ELECTRICAL SPECIFICATIONS PER DIODE</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	$V_{BR}$	I <sub>R</sub> = 100 μA		600	-	-	
Farmer durable and	I <sub>F</sub> = 30 A		-	1.32	1.69		
	V	I <sub>F</sub> = 60 A		-	1.52	1.9	V
Forward voltage	$V_{FM}$	I <sub>F</sub> = 30 A	T <sub>J</sub> = 125 °C	-	1.14	1.39	
		I <sub>F</sub> = 60 A		-	1.38	1.66	
Reverse leakage current I <sub>RM</sub>		$V_R = V_R$ rated		-	0.1	50	μA
		T <sub>J</sub> = 175 °C, V <sub>R</sub> = V <sub>R</sub> rated		-	0.2	1.0	mA
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 600 V		-	30	-	pF

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 1 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 30 V	-	34	-	- ns
neverse recovery time		T <sub>J</sub> = 25 °C	$I_F = 30 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	79	-	
		T <sub>J</sub> = 125 °C		-	155	-	
Peak recovery current		T <sub>J</sub> = 25 °C		-	6	-	A
	IRRM	T <sub>J</sub> = 125 °C		-	14	-	
Reverse recovery charge Q <sub>rr</sub>	0	T <sub>J</sub> = 25 °C		-	234	-	nC
	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	1085	-	TIC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction to case, single leg conducting	Ь		-	-	1.02	
Junction to case, both leg conducting	R <sub>thJC</sub>		-	-	0.51	°C/W
Case to heatsink	R <sub>thCS</sub>	Flat, greased surface	-	0.10	-	
Weight			-	30	-	g
Mounting torque			-	-	1.3	Nm
Case style				SOT	-227	





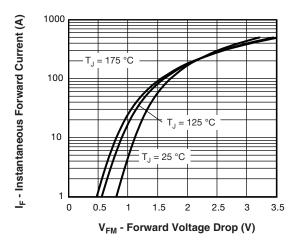


Fig. 1 - Typical Forward Voltage Drop Characteristics (Per Diode)

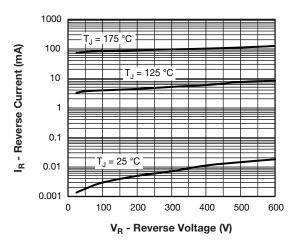


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

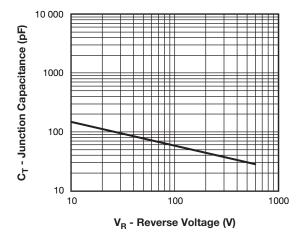


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

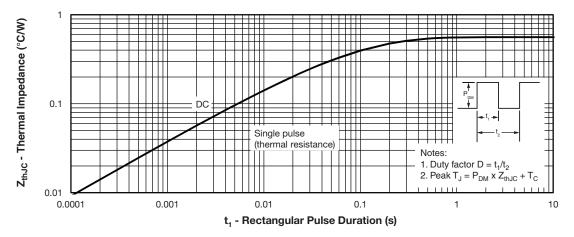


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics (Per Diode)

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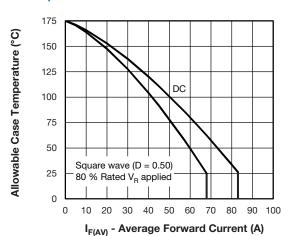


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current (Per Leg)

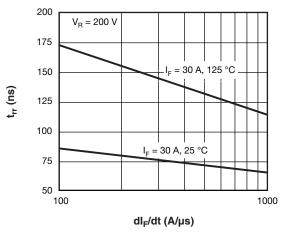


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

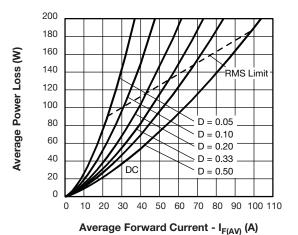


Fig. 6 - Forward Power Loss Characteristics (Per Leg)

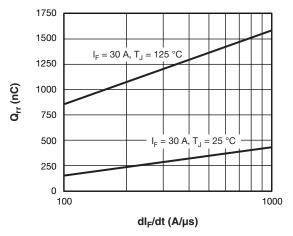


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

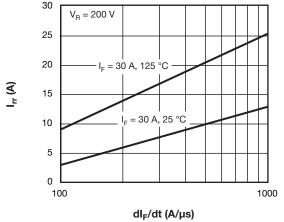


Fig. 9 - Typical Stored Current vs. dl<sub>F</sub>/dt

#### Note

 $^{(1)}$  Formula used: T<sub>C</sub> = T<sub>J</sub> - (Pd + Pd<sub>REV</sub>) x R<sub>thJC</sub>; Pd = Forward power loss = I<sub>F(AV)</sub> x V<sub>FM</sub> at (I<sub>F(AV)</sub>/D) (see fig. 6); Pd<sub>REV</sub> = Inverse power loss = V<sub>R1</sub> x I<sub>R</sub> (1 - D); I<sub>R</sub> at V<sub>R1</sub> = 80 % rated V<sub>R</sub>

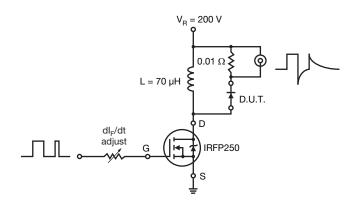
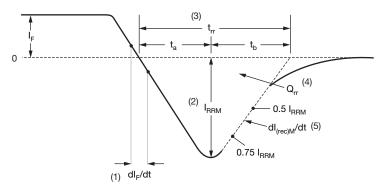


Fig. 10 - Reverse Recovery Parameter Test Circuit



- (1) dI<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

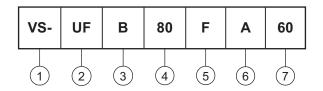
Fig. 11 - Reverse Recovery Waveform and Definitions



### Vishay Semiconductors

### **ORDERING INFORMATION TABLE**

**Device code** 



- Vishay Semiconductors product
- 2 Ultrafast rectifier
- 3 Ultrafast Pt diffused
- 4 Current rating (80 = 80 A)
- 5 Circuit configuration (2 separate diodes, parallel pin-out)
- Package indicator (SOT-227 standard insulated base)
- 7 Voltage rating (60 = 600 V)

CIRCUIT CONFIGURATION						
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING				
2 separate diodes, parallel pin-out	F	Lead Assignment  4 0 0 3 4 1 0 0 2 1				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95423				
Packaging information	www.vishay.com/doc?95425				



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